Jana Schaber<sup>1,2</sup>, R. Xiang<sup>2</sup>, J.Teichert<sup>2</sup>, P.Murcek<sup>2</sup>, P.Zwartek<sup>2</sup>, A.Arnold<sup>2</sup>, A.Rhyzov<sup>2</sup>, S.Ma<sup>2</sup>, N.Gaponik<sup>1</sup>



<sup>1</sup> Helmholtz-Centre Dresden-Rossendorf, Dresden, Germany
 <sup>2</sup> Technical University Dresden, Dresden, Germany

HELMHOLTZ ZENTRUM DRESDEN ROSSENDORF

## **GaN:Cs Photocathode for SRF Guns**

### Method

- p-type GaN (magnesium doped) on sapphire or other substrate is studied
- Wet chemical pre-cleaning to remove dust and organic parts from the surface (analysis with AFM measurements)
- The GaN is transferred into UHV chamber via portable suitcase



In UHV chamber the GaN undergoes a cycle process, which consists of the following steps:



- QE tracking of the prepared GaN:Cs photocathode over time till it drops to zero
- → Starting again with thermal treating and activation process (re-activation)

#### Quantum efficiency (QE)

 The released photoelectrons enter into the vacuum and are collected by a copper ring anode

Fig. 1: experimental set-up inside of GaN UHV-chamber

#### 2. Cs-activation

Fig. 2: scheme of cycle process

 Thermal treatment at certain temperature to desorb residual gases
 deposition of caesium on clean surface while illuminating with UV-

light

• The number of released photoelectrons in ratio of the input photons of UV-light derives in the quantum efficiency (QE)

$$QE = \frac{N_{photoelectrons}}{N_{photons of UV-light}}$$
 (1)

$$QE = \frac{h \cdot c}{q_e \cdot \lambda} \cdot \frac{I}{P_{UV-light}} \qquad (2)$$

#### Results

#### GaN on silicon



# QE decay curves of GaN on silicon (#2020.06) (500°C)

#### **SEM Image**





Fig. 4: QE tracking from GaN on silicon

# 30 μm EHT = 20.00 kV Stage at T = 0.0° Mag = 300 X WD = 6.2 mm Tilt Angle = 0.0° Signal A = SESI 12 Nov 2020

#### Fig. 5: SEM image of used GaN on silicon

#### GaN on sapphire

Fig. 3: photocurrent activation curves for GaN on silicon







time [min]

Fig. 6: photocurrent activation curves for GaN on sapphire

Fig. 7: QE tracking of GaN on sapphire

Fig. 8: QE comparison of all activated GaN samples

### Outlook

Activation of GaN with caesium and lifetime observation

- on other substrate (SiC)
- use better conductive samples (gold sputtering)
- compare to selfmade GaN (Uni Siegen)



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#### Fig. 9: combination of GaN chamber and XPS



M. Sc. Jana Schaber · j.schaber@hzdr.de · www.hzdr.de



600





time [h]